**Product data sheet** 

## 1. General description

Dual common cathode power Schottky diode designed for high frequency switched mode power supplies in a TO220F plastic package.





### 2. Features and benefits

- · Trench structure
- High junction temperature up to 150°C
- · Low forward voltage drop, negligible switching losses
- High efficiency

## 3. Applications

- DC to DC converters
- · Freewheeling diode
- OR-ing diode
- Switched mode power supply rectifier

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Notes		Values		Unit		
Absolute	Absolute maximum rating								
$V_{RRM}$	repetitive peak reverse voltage				120		V		
$I_{F(AV)}$	average forward current	$\delta$ = 0.5 ; square-wave pulse; per diode; Fig. 1; Fig. 2; Fig. 3			20		А		
$I_{O(AV)}$	average output current	$\delta$ = 0.5 ; square-wave pulse; both diodes conducting			40		А		
Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit		
Static ch	Static characteristics								
$V_{F}$	forward voltage	$I_F = 20 \text{ A}$ ; $T_j = 25 \text{ °C}$ ; per diode; Fig. 6		-	0.95	1.05	V		
I <sub>R</sub>	reverse current	$V_R = 120 \text{ V}$ ; $T_j = 25 \text{ °C}$ ; per diode; Fig. 7; Fig. 8		-	4	20	μΑ		

# 5. Pinning information

**Table 2. Pinning information** 

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A1	anode 1	mb	
2	K	cathode		A1 A2
3	A2	anode 2		Κ Κ sym125
mb	n.c.	mounting base; isolated		sym 25

## 6. Ordering information

#### **Table 3. Ordering information**

Type number	Package name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
WN3S40120CX	TO220F	WN3S40120CXQ	Tube	50	SOT186A	14-Nov-2013

## 7. Marking

### Table 4. Marking codes

Type number	Marking codes
WN3S40120CX	WN3S40 120CX

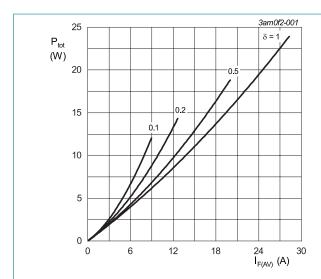
## 8. Limiting values

### **Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

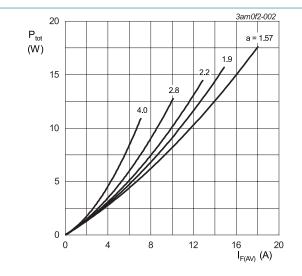
Symbol	Parameter	Conditions	Notes	Values	Unit
$V_{RRM}$	repetitive peak reverse voltage			120	V
$V_{RWM}$	crest working reverse voltage			120	V
$V_R$	reverse voltage	DC		120	V
$I_{F(AV)}$	average forward current	$\delta$ = 0.5; square-wave pulse; per diode; Fig. 1; Fig. 2; Fig. 3		20	А
$I_{O(AV)}$	average output current	$\delta$ = 0.5; square-wave pulse; both diodes conducting		40	А
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode; Fig. 4		330	А
		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode		363	А
T <sub>stg</sub>	storage temperature			-40 to 150	°C
T <sub>j</sub>	junction temperature		[1]	-40 to 150	°C

[1] The heat generated must be less than the thermal conductivity from Junction to Ambient:  $dP_{tot}/dT_j < 1/R_{th(j-a)}$ 



 $\begin{aligned} & I_{F(AV)} = I_{F(RMS)} \times \sqrt{\delta} \\ & V_o = 0.614 \text{ V}; \text{ R}_s = 0.0082 \text{ } \Omega \end{aligned}$ 

Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values; per diode



a = form factor =  $I_{F(RMS)} / I_{F(AV)}$  $V_o$  = 0.614 V;  $R_s$  = 0.0082  $\Omega$ 

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values; per diode

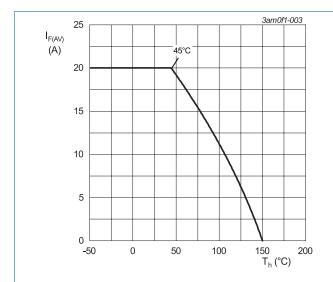


Fig. 3. Average forward current as a function of heatsink temperature; maximum values; per diode

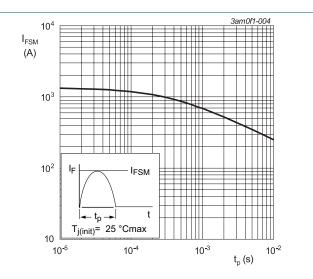


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values; per diode

### 9. Thermal characteristics

#### **Table 6. Thermal characteristics**

Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
R <sub>th(j-h)</sub>	thermal resistance from junction to	with heatsink compound; per diode; Fig. 5		-	-	5.6	K/W
heatsink	heatsink	with heatsink compound; both diodes conducting		-	-	4.3	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient free air	in free air		-	60	-	K/W

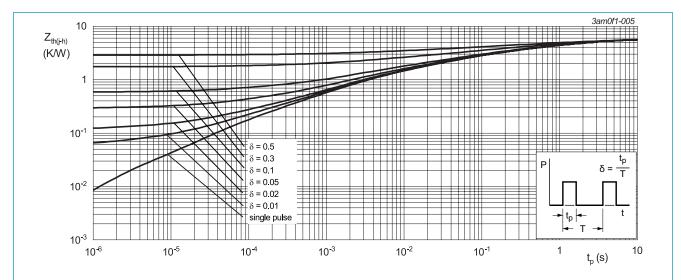


Fig. 5. Transient thermal impedance from junction to heatsink as a function of pulse duration; maximum values; per diode

### 10. Isolation characteristics

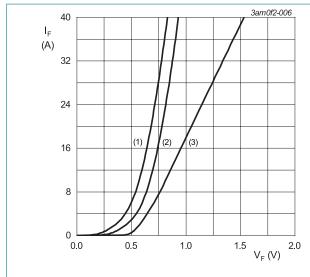
#### **Table 7. Isolation characteristics**

Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
V <sub>isol(RMS)</sub>	RMS isolation voltage	from all terminals to external heatsink; sinusoidal waveform; clean and dust free; $50 \text{ Hz} \le f \le 60 \text{ Hz}$ ; $T_h = 25 ^{\circ}\text{C}$ ; RH $\le 65 ^{\circ}\text{M}$		-	-	2500	V

## 11. Characteristics

**Table 8. Characteristics** 

Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
Static ch	aracteristics						
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 20 A; T <sub>j</sub> = 25 °C; per diode; <u>Fig. 6</u>		-	0.95	1.05	V
		I <sub>F</sub> = 20 A; T <sub>j</sub> = 125 °C; per diode; <u>Fig. 6</u>		-	0.72	-	V
		I <sub>F</sub> = 15 A; T <sub>j</sub> = 25 °C; per diode; <u>Fig. 6</u>		-	0.82	-	V
		I <sub>F</sub> = 15 A; T <sub>j</sub> = 125 °C; per diode; <u>Fig. 6</u>		-	0.66	-	V
		I <sub>F</sub> = 2 A; T <sub>j</sub> = 25 °C; per diode; <u>Fig. 6</u>		-	0.47	-	V
		I <sub>F</sub> = 2 A; T <sub>j</sub> = 125 °C; per diode; <u>Fig. 6</u>		-	0.39	-	V
I <sub>R</sub>	reverse current	$V_R = 120 \text{ V}; T_j = 25 ^{\circ}\text{C}; \text{ per diode}; $ Fig. 7; Fig. 8		-	4	20	μA
		V <sub>R</sub> = 120 V; T <sub>j</sub> = 125 °C; per diode; Fig. 7; Fig. 8		-	3	20	mA

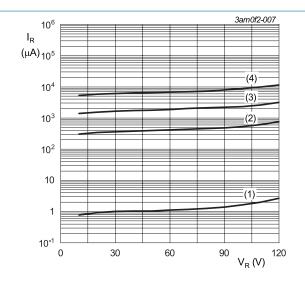


 $V_o$  = 0.614 V;  $R_s$  = 0.0082  $\Omega$ 

(1)  $T_j$  = 150 °C; typical values (2)  $T_j$  = 150 °C; maximum values

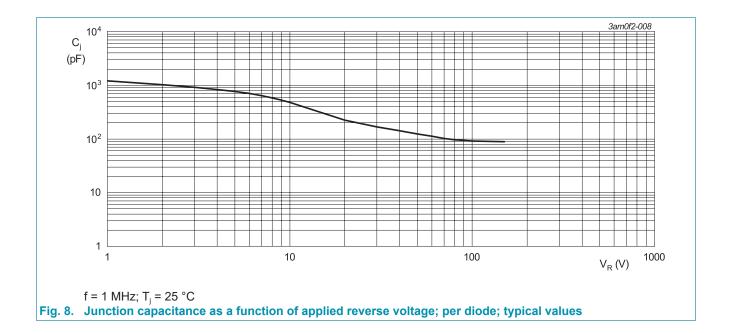
(3) T<sub>i</sub> = 25 °C; maximum values

Fig. 6. Forward current as a function of forward voltage; per diode

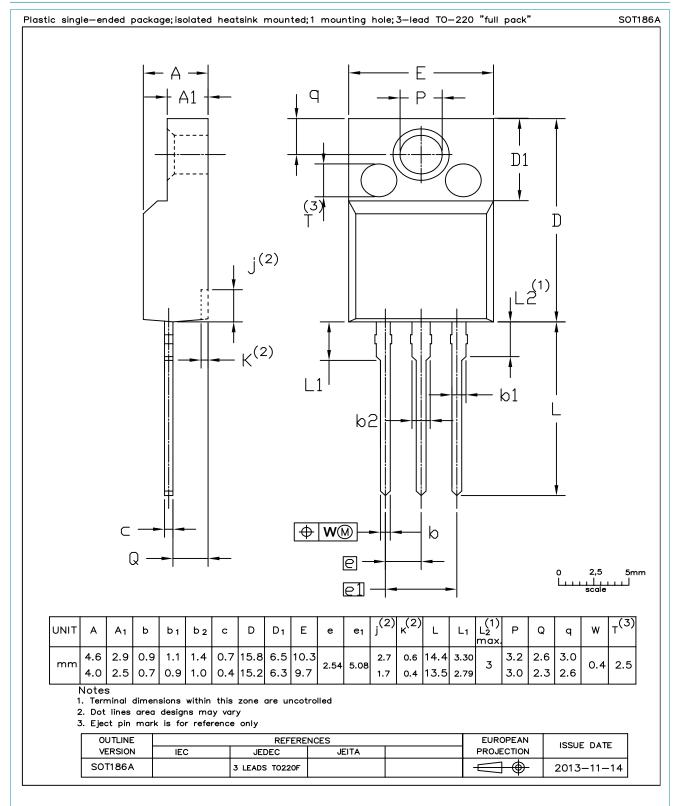


(1)  $T_j$  = 25 °C; typical values (2)  $T_j$  = 100 °C; typical values (3)  $T_j$  = 125 °C; typical values (4)  $T_j$  = 150 °C; typical values

Fig. 7. Reverse leakage current as a function of reverse voltage; per diode; typical values



## 12. Package outline



## 13. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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